

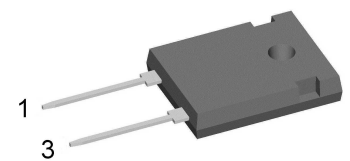
# Sonic Fast Recovery Diode

$V_{RRM} = 1200\text{ V}$   
 $I_{FAV} = 30\text{ A}$   
 $t_{rr} = 200\text{ ns}$

High Performance Fast Recovery Diode  
 Low Loss and Soft Recovery  
 Single Diode

Part number

**DHG30I1200HA**



Backside: cathode



## Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low  $I_{rm}$ -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low  $I_{rm}$  reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

## Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

## Package: TO-247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

## Disclaimer Notice

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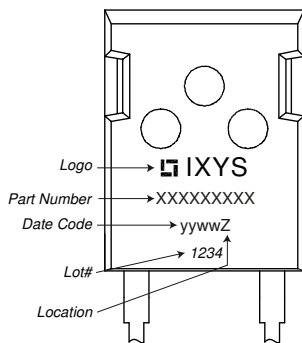


Fast Diode				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$V_{RSM}$	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			1200	V	
$V_{RRM}$	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			1200	V	
$I_R$	reverse current, drain current	$V_R = 1200 V$	$T_{VJ} = 25^{\circ}C$		50	$\mu A$	
		$V_R = 1200 V$	$T_{VJ} = 125^{\circ}C$		0.5	mA	
$V_F$	forward voltage drop	$I_F = 30 A$	$T_{VJ} = 25^{\circ}C$		2.26	V	
		$I_F = 60 A$			3.00	V	
		$I_F = 30 A$	$T_{VJ} = 125^{\circ}C$		2.27	V	
		$I_F = 60 A$			3.20	V	
$I_{FAV}$	average forward current	$T_C = 90^{\circ}C$ rectangular $d = 0.5$	$T_{VJ} = 150^{\circ}C$		30	A	
$V_{FO}$	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}C$		1.25	V	
$r_F$	slope resistance				30	m $\Omega$	
$R_{thJC}$	thermal resistance junction to case				0.7	K/W	
$R_{thCH}$	thermal resistance case to heatsink			0.3		K/W	
$P_{tot}$	total power dissipation		$T_C = 25^{\circ}C$		180	W	
$I_{FSM}$	max. forward surge current	$t = 10 ms; (50 Hz), sine; V_R = 0 V$	$T_{VJ} = 45^{\circ}C$		200	A	
$C_J$	junction capacitance	$V_R = 600 V$ $f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		11	pF	
$I_{RM}$	max. reverse recovery current	} $I_F = 30 A; V_R = 600 V$ $-di_F / dt = 600 A/\mu s$	$T_{VJ} = 25^{\circ}C$		23	A	
			$T_{VJ} = 125^{\circ}C$		30	A	
$t_{rr}$	reverse recovery time		$T_{VJ} = 25^{\circ}C$		200	ns	
			$T_{VJ} = 125^{\circ}C$		350	ns	



Package TO-247			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			70	A
$T_{VJ}$	virtual junction temperature		-55		150	°C
$T_{op}$	operation temperature		-55		125	°C
$T_{stg}$	storage temperature		-55		150	°C
<b>Weight</b>				6		g
$M_D$	mounting torque		0.8		1.2	Nm
$F_C$	mounting force with clip		20		120	N

**Product Marking**



**Part description**

- D = Diode
- H = Sonic Fast Recovery Diode
- G = extreme fast
- 30 = Current Rating [A]
- I = Single Diode
- 1200 = Reverse Voltage [V]
- HA = TO-247AD (2)

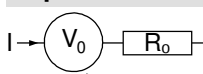
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DHG30I1200HA	DHG30I1200HA	Tube	30	503098

Similar Part	Package	Voltage class
DSEP30-12A	TO-247AD (2)	1200
DSEP29-12A	TO-220AC (2)	1200
DSEP30-12AR	ISOPLUS247 (2)	1200
DSEP30-12CR	ISOPLUS247 (2)	1200

**Equivalent Circuits for Simulation**

\* on die level

$T_{VJ} = 150^{\circ}C$

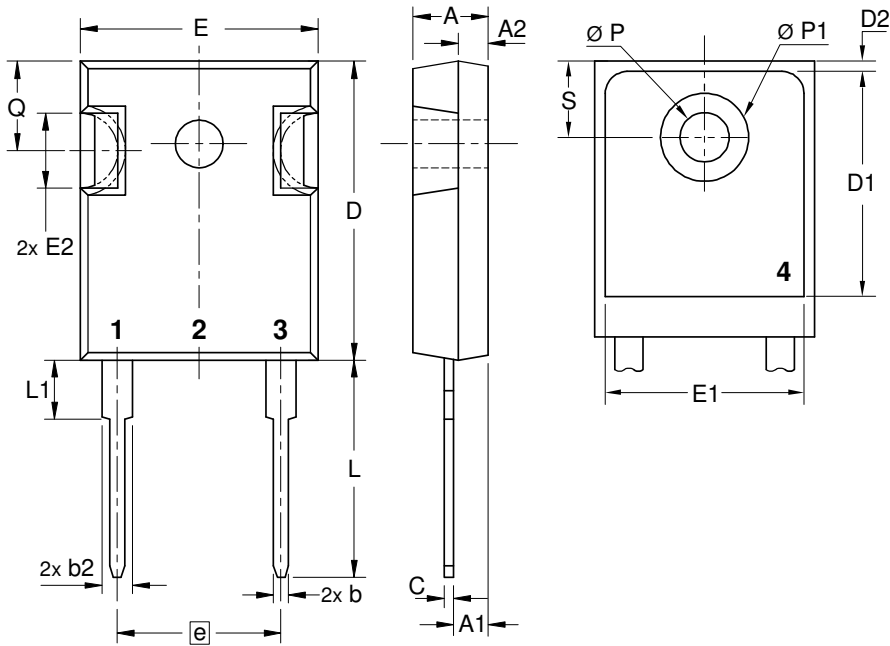


**Fast Diode**

$V_{0\ max}$	threshold voltage	1.25	V
$R_{0\ max}$	slope resistance *	27	mΩ



**Outlines TO-247**



Sym.	Inches		Millimeter	
	min.	max.	min.	max.
A	0.185	0.209	4.70	5.30
A1	0.087	0.102	2.21	2.59
A2	0.059	0.098	1.50	2.49
D	0.819	0.845	20.79	21.45
E	0.610	0.640	15.48	16.24
E2	0.170	0.216	4.31	5.48
e	0.430 BSC		10.92 BSC	
L	0.780	0.800	19.80	20.30
L1	-	0.177	-	4.49
Ø P	0.140	0.144	3.55	3.65
Q	0.212	0.244	5.38	6.19
S	0.242 BSC		6.14 BSC	
b	0.039	0.055	0.99	1.40
b2	0.065	0.094	1.65	2.39
b4	0.102	0.135	2.59	3.43
c	0.015	0.035	0.38	0.89
D1	0.515	-	13.07	-
D2	0.020	0.053	0.51	1.35
E1	0.530	-	13.45	-
Ø P1	-	0.29	-	7.39



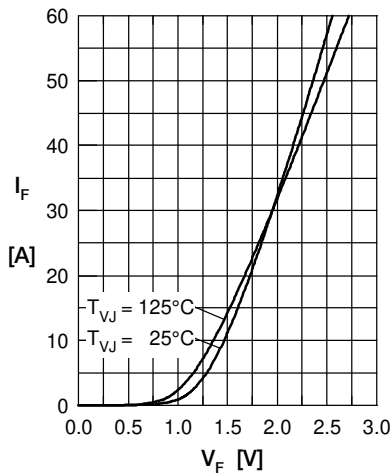
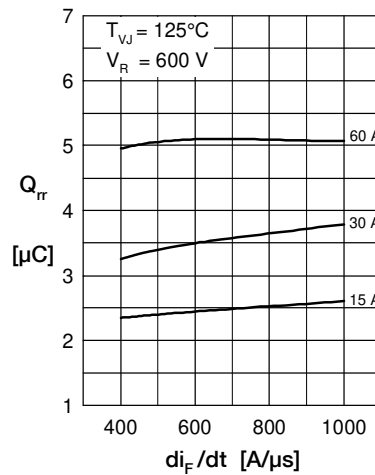
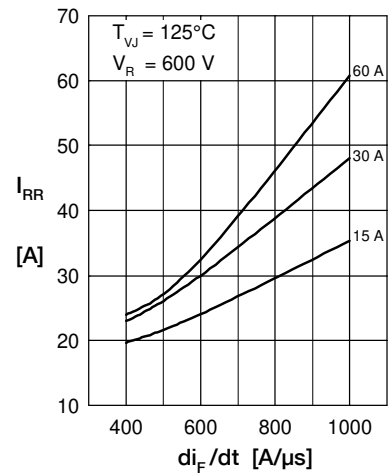
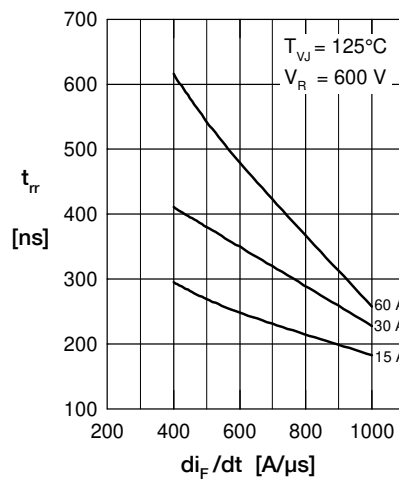
**Fast Diode**

 Fig. 1 Typ. Forward current versus  $V_F$ 

 Fig. 2 Typ. reverse recov. charge  $Q_{rr}$  versus di/dt

 Fig. 3 Typ. peak reverse current  $I_{RRM}$  versus di/dt

 Fig. 4 Dynamic parameters  $Q_{rr}$ ,  $I_{RRM}$  versus  $T_{VJ}$ 

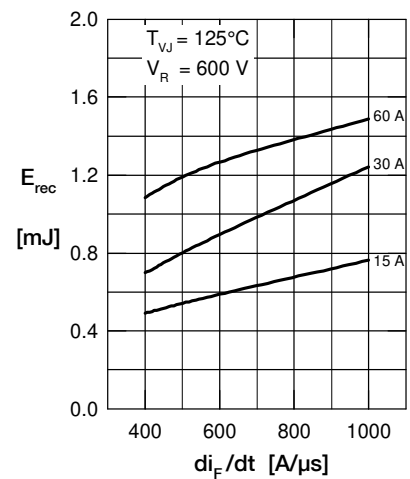
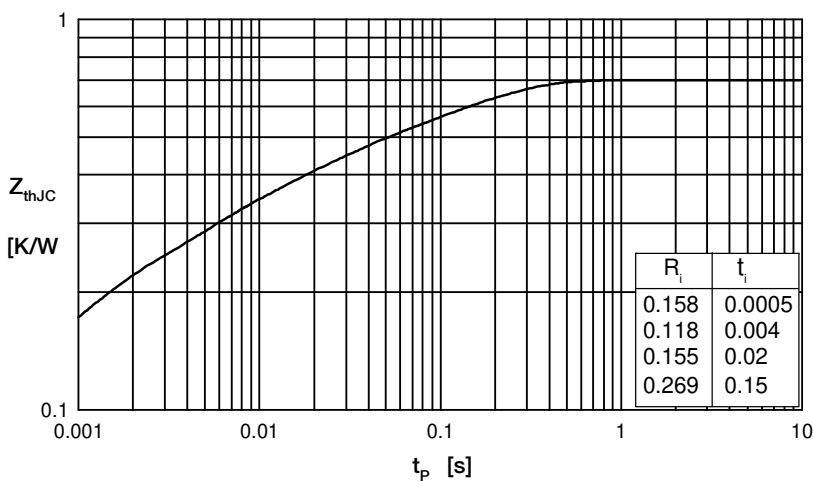
 Fig. 5 Typ. recovery time  $t_{rr}$  versus di/dt

 Fig. 6 Typ. recovery energy  $E_{rec}$  versus di/dt


Fig. 7 Typ. transient thermal impedance junction to case

单击下面可查看定价，库存，交付和生命周期等信息

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